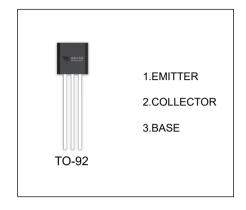


KSA539 TRANSISTOR (PNP)

FEATURES

- Low Saturation Medium Current Application
- Complement to KSC815



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
KSA539	TO-92	Bulk	1000pcs/Bag
KSA539-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage		V
V _{CEO}	V cEO Collector-Emitter Voltage V EBO Emitter-Base Voltage Ic Collector Current P c Collector Power Dissipation		V
V _{EBO}			V
Ic			Α
Pc			mW
R ₀ JA	R _{θ JA} Thermal Resistance From Junction To ambient		°C/W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C



$T_a \text{=} 25\,^\circ\!\!\subset\,$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =- 0.1mA,I _E =0	-60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-10mA,I _B =0	-45			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-0.01mA,I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-45V,I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-3V,I _C =0			-0.1	μA
DC current gain	h _{FE}	V _{CE} =-1V, I _C =-50mA	40		240	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-150mA,I _B =-15mA			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-150mA,I _B =-15mA			-1.2	V
Base-emitter voltage	V _{BE}	V _{CE} =-1V, I _C =-10mA	-0.6		-0.9	V

CLASSIFICATION OF h_{FE}

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RANK	R	0	Υ		
RANGE	40-80	70-140	120-240		